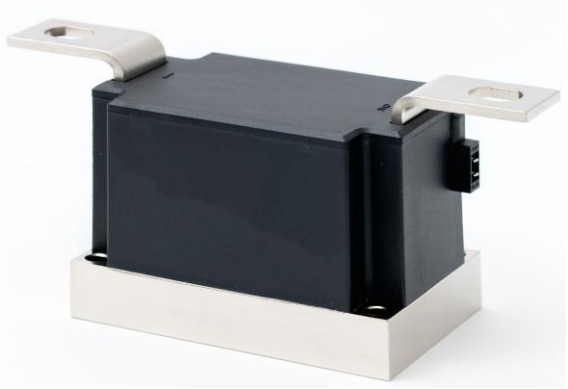
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Diode module

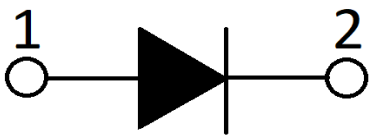


Features:

- International standard package
- Low forward voltage drop
- Isolation voltage 3000V ~
- Simple mounting

Typical applications:

- Various rectifier power
- AC/DC motor control
- Heater control
- Frequency converters



Symbol	Characteristcs	Test Conditions	Value			Unit
			Min	Typ	Max	
V_{RSM}	Non-repetitive reverse blocking voltage	Tj = 25°C			2700	V
V_{RRM}	Repetitive reverse blocking voltage	Tj = 25°C			2600	V
$I_{F(AV)}$	Forward average current	180° half sine wave 50Hz T_c = 105°C (100°C)			1080 (1200)	A
$I_{F(RMS)}$	Forward square root current	180° half sine wave 50Hz T_c = 100 °C			1884	A
I_{RRM}	Repetitive peak current	at V_{RRM} Tj = 150°C			50	mA
I_{FSM}	Forward surge current	10ms half sine wave, V_R = 0.6V, Tj = 150°C			30000	A
I^2t	I^2t for fusing coordination	10ms half sine wave, V_R = 0.6V, Tj = 150°C			4500000	A^2s
V_{FO}	Threshold voltage	Tj = 150°C			0.70	V
r_T	Forward slope resistance	Tj = 150°C			0.10	mΩ
V_{FM}	Peak forward voltage	Tj = 25°C ; I_F = 3000A			1.30	V
$R_{th(j-c)}$	Thermal resistance junction to case	Single side cooled per chip			0.042	°C/W
$R_{th(c-s)}$	Thermal resistance case to sink	Single side cooled per chip			0.020	°C/W
V_{ISO}	Isolation voltage	50Hz, RMS, t = 1min	3000			V
F_M	Mounting torque - copper plate (M6)		4.5		6.0	N·m
	Mounting torque - terminal (M12)		12.0		14.0	N·m
T_{stg}	Storage Temperature		-40		+125	°C
T_j	Operating Temperature		-40		+150	°C
W_t	Weight			2700		g
Outline	432F2					

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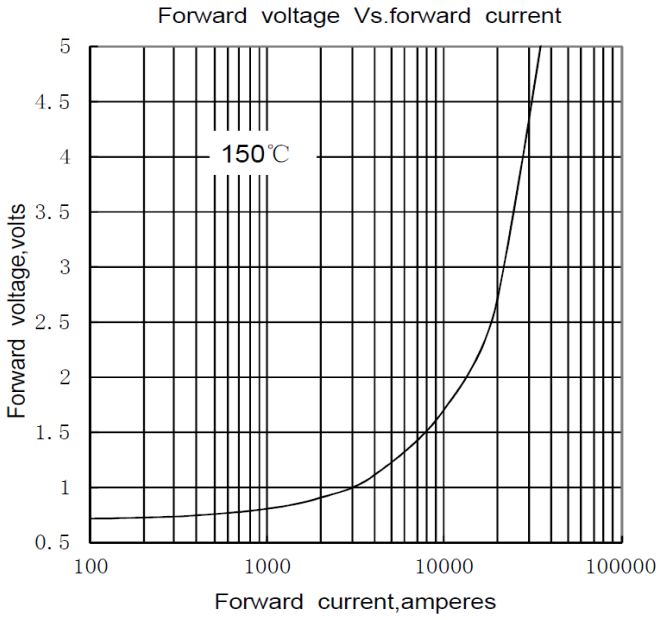


Fig.1

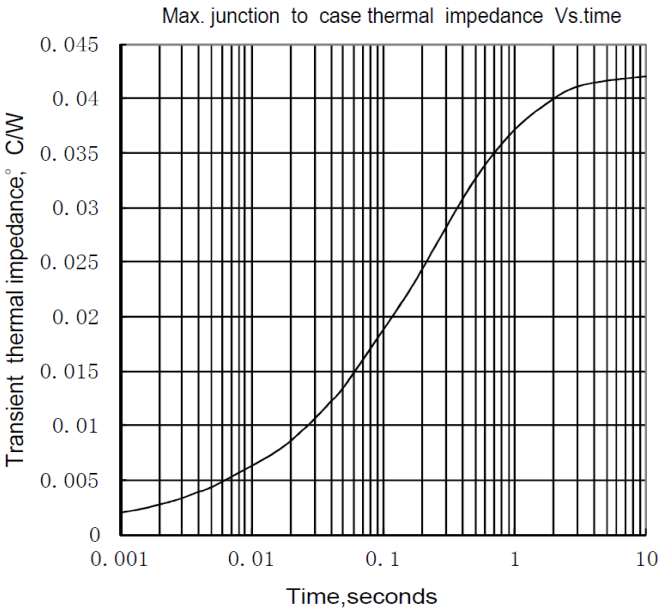


Fig.2

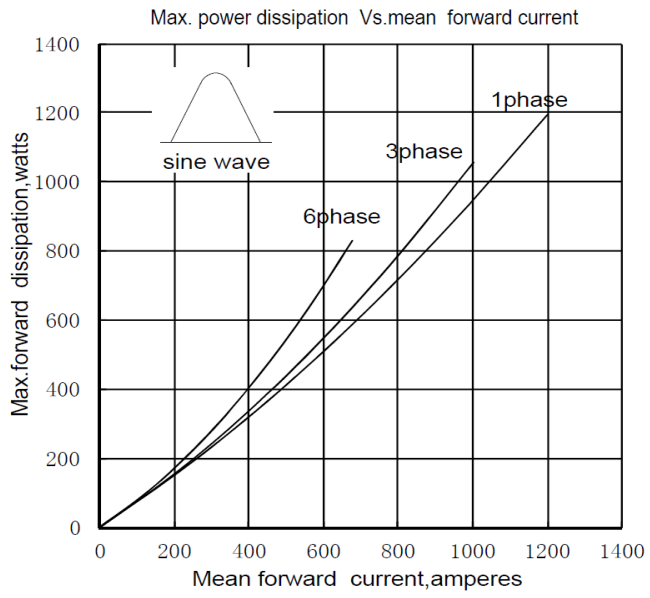


Fig.3

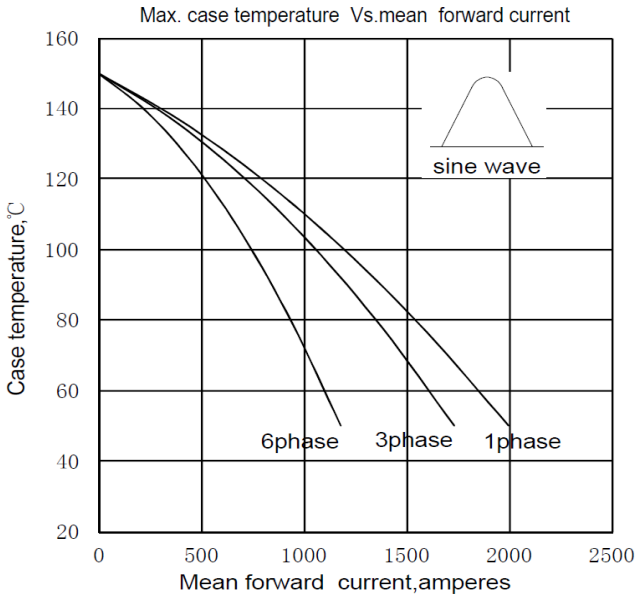


Fig.4

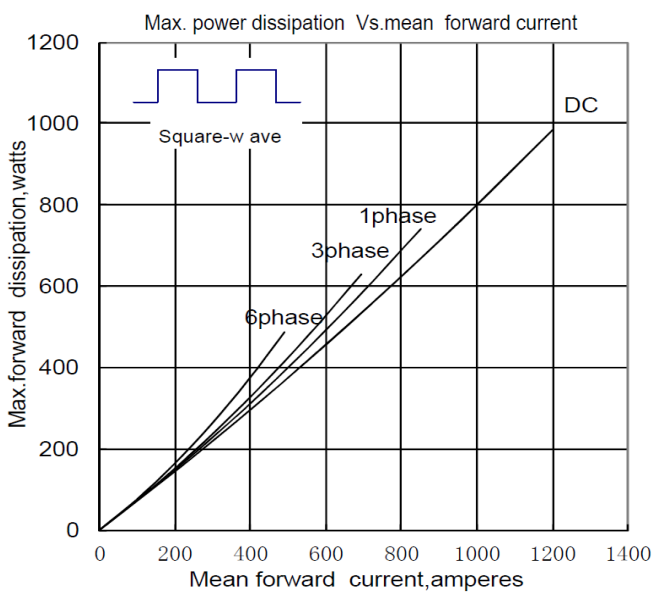


Fig.5

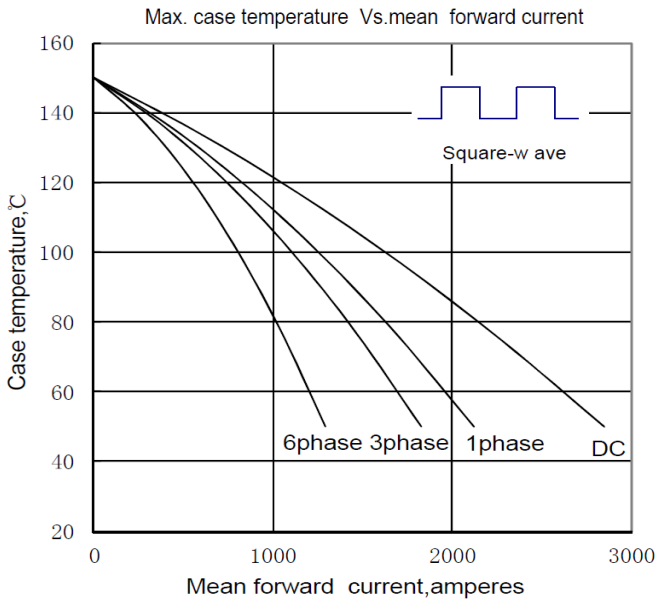


Fig.6

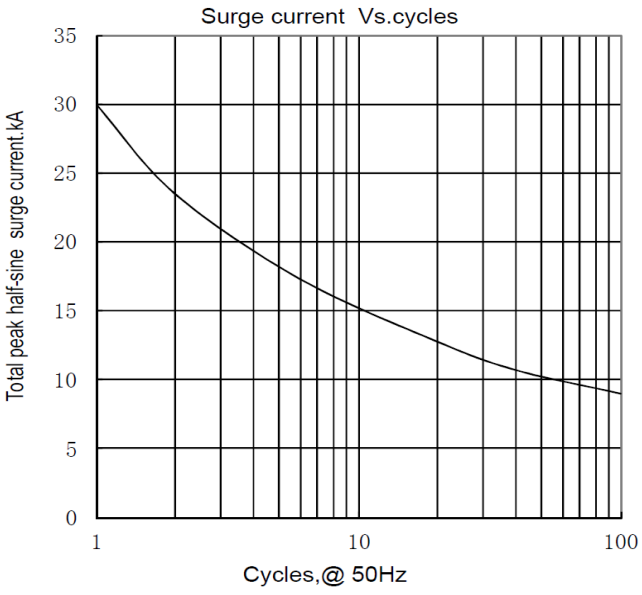


Fig.7

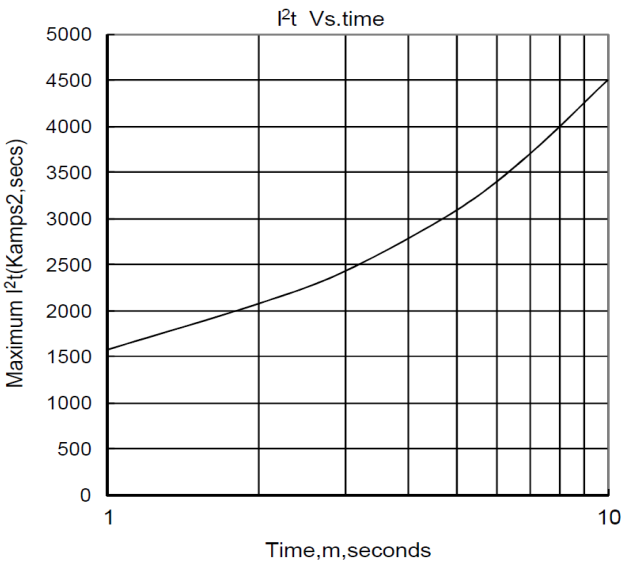
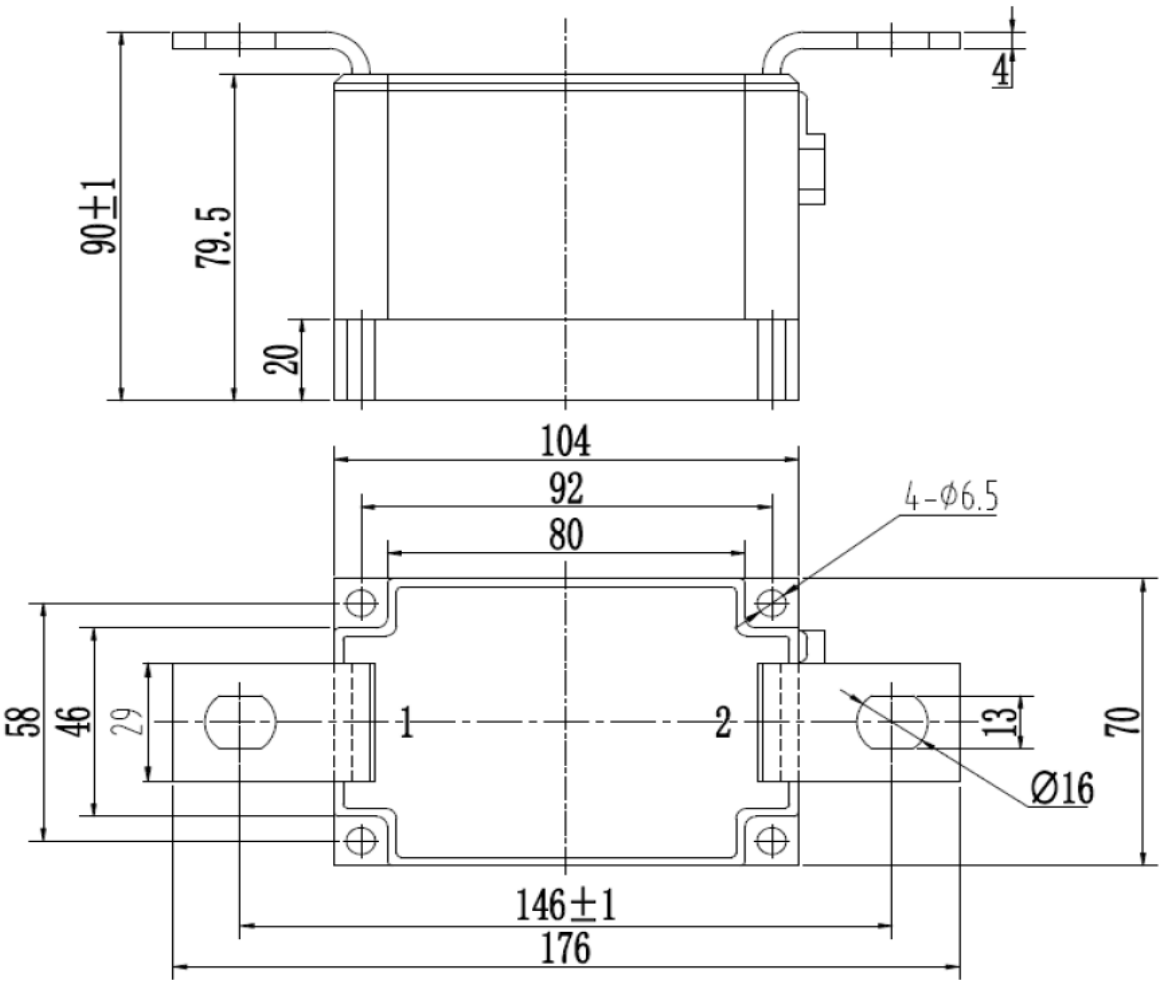


Fig.8

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(dimensions in mm)

S.CO.M.E.S. Srl
Via Enrico Mattei, 6/8 - 26283 - Castiglione d'Adda (LO) - Italy
Phone: +39 0377 901243 Fax: +39 0377 900206

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